

The documentation and process conversion measures necessary to comply with this revision shall be completed by 15 August 2014.

INCH-POUND

MIL-PRF-19500/597G
17 May 2014
SUPERSEDING
MIL-PRF-19500/597F
27 January 2014

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, TRANSISTORS, QUAD, FIELD EFFECT,
N-CHANNEL, SILICON, TYPE 2N7334,
JAN, JANTX, JANTXV, JANS, JANHC, AND JANKC

This specification is approved for use by all Departments
and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of
this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

1.1 Scope. This specification covers the performance requirements for quad N-channel, enhancement-mode, MOSFET, power transistor with avalanche energy ratings (E_{AS} and E_{AR}) and maximum avalanche current (I_{AR}). Four levels of product assurance are provided for each hermetic encapsulated device type as specified in [MIL-PRF-19500](#). Two levels of product assurance are provided for each unencapsulated device type (die) as specified in [MIL-PRF-19500](#).

1.2 Physical dimensions. The device package styles are as follows: 14 pin dual-in line package (MO-036AB) in accordance with [figure 1](#) and unencapsulated die in accordance with [figures 2](#) and [3](#) for device types JANHC and JANKC.

1.3 Maximum ratings. Unless otherwise specified, $T_A = +25^\circ\text{C}$.

P_T (1) $T_C = +25^\circ\text{C}$ (free air)		V_{GS}	I_{D1} (2) (3) $T_C = +25^\circ\text{C}$		I_{D2} (2) $T_C = +100^\circ\text{C}$	I_S	E_{AS}	E_{AR}
(1 die)	(4 die)							
<u>W</u>	<u>W</u>	<u>V dc</u>	<u>A dc</u>		<u>A dc</u>	<u>A dc</u>	<u>mj</u>	<u>mj</u>
1.4	2.5	± 20	1.0		0.6	1.0	75	0.14

I_{AR} (2)	I_{DM} (4)	T_{OP} and T_{STG}	Maximum $r_{DS(on)}$ (1) $V_{GS} = 10 \text{ V dc}$, $I_D = I_{D2}$		$R_{\theta JA1}$ maximum (1 die)	$R_{\theta JA2}$ maximum (4 die)	$R_{\theta JC}$ maximum (1 die)
			$T_J = +25^\circ\text{C}$	$T_J = +150^\circ\text{C}$			
<u>A</u>	<u>A(pk)</u>	<u>$^\circ\text{C}$</u>	<u>ohm</u>	<u>ohm</u>	<u>$^\circ\text{C/W}$</u>	<u>$^\circ\text{C/W}$</u>	
1.0	4.0	-55 to +150	0.70	1.4	90	50	

Comments, suggestions, or questions on this document should be addressed to DLA Land and Maritime, ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to Semiconductor@dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil>.

- (1) Derate linearly 11 mW/°C for $T_c > +25^\circ\text{C}$ for one die.
 (2) The following formula derives the maximum theoretical I_D limit. I_D is limited by package and internal wires and may also be limited by pin diameter:

$$I_D = \sqrt{\frac{T_{JM} - T_C}{(R_{\theta JC}) \times (R_{DS(ON)} \text{ at } T_{JM})}}$$

- (3) See [figure 4](#), maximum drain current graph.
 (4) $I_{DM} = 4 I_{D1}$; I_{D1} as calculated in note (2).

1.4 Primary electrical characteristics. Unless otherwise specified, $T_c = +25^\circ\text{C}$.

Type	Minimum $V_{(BR)DSS}$ $V_{GS} = 0 \text{ V}$ $I_D = 1 \text{ mA dc}$	$V_{GS(th)1}$ $V_{DS} \geq V_{GS}$ $I_D = 0.25 \text{ mA}$	Maximum I_{DSS1} $V_{GS} = 0 \text{ V}$ $V_{DS} = 80 \text{ percent}$ of rated V_{DS}	Maximum $r_{DS(on)1}$ (1) $V_{GS} = 10 \text{ V dc}$ $I_D = I_{D2}$ $T_J = +25^\circ\text{C}$
	<u>V dc</u>	V dc <u>Min</u> <u>Max</u>	<u>μA dc</u>	<u>ohms</u>
2N7334	100	2.0 4.0	25	0.70

- (1) Pulsed (see [4.5.1](#)).

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections [3](#) and [4](#) of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections [3](#) and [4](#) of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

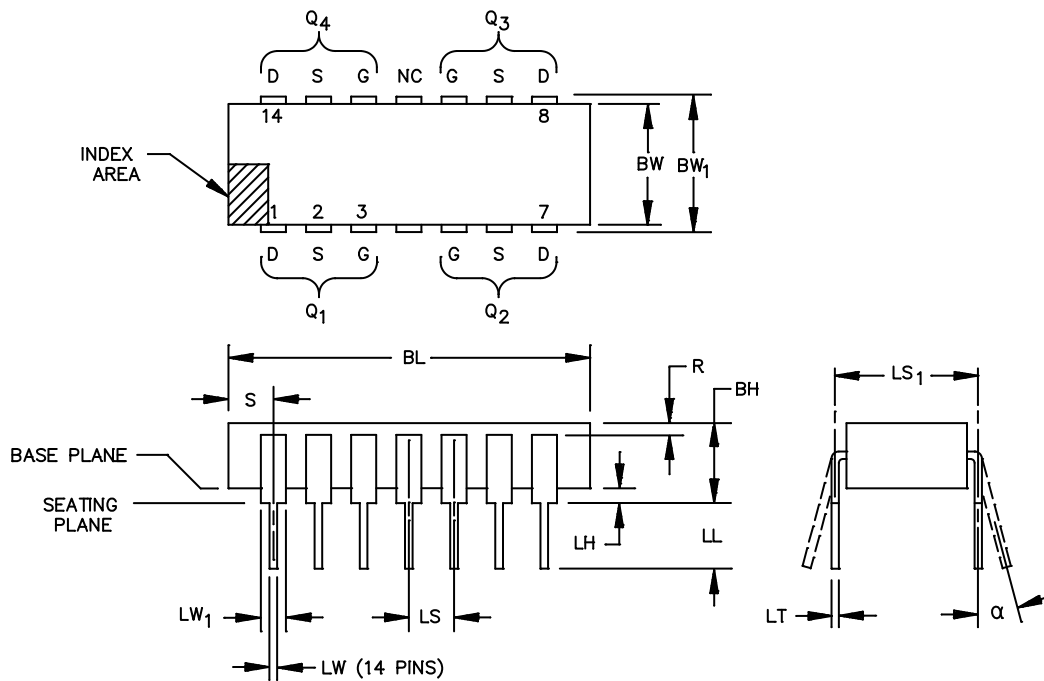
[MIL-PRF-19500](#) – Semiconductor Devices, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

[MIL-STD-750](#) – Test Methods for Semiconductor Devices.

(Copies of these documents are available online at <http://quicksearch.dla.mil>.)

2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.



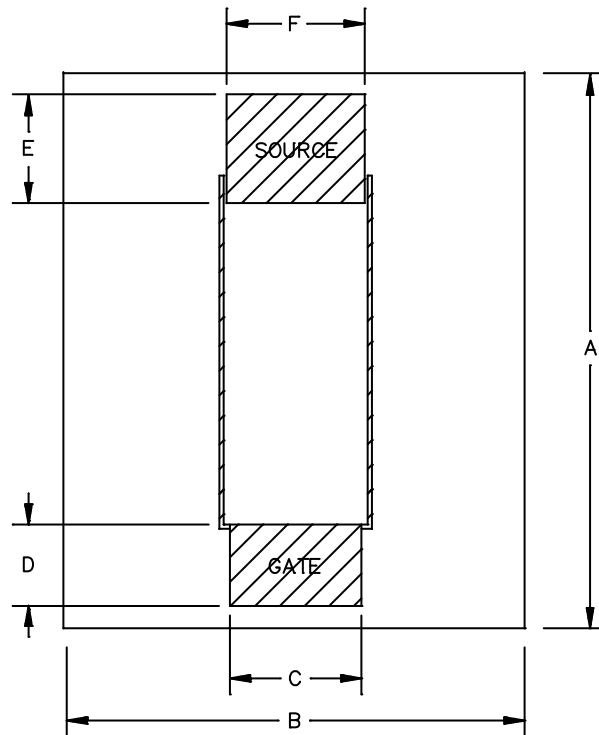
Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
BH	.105	.175	2.67	4.45	4
BL	.690	.770	17.53	19.56	
BW	.280	.310	7.11	7.87	
BW ₁	.290	.325	7.37	8.26	5
LH	.025	.055	0.64	1.40	4, 6
LL	.125	.175	3.18	4.45	4
LT	.008	.012	0.203	0.305	

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
LS	.100 TP		2.54 TP		7
LS ₁	.300 TP		7.62 TP		7
LW	.015	.021	0.381	0.533	6
LW ₁	.038	.060	0.97	1.52	
R	.010		0.25		
S	.030	.095	0.76	2.41	
α	0°	15°	0°	15°	8

NOTES:

1. Dimensions are in inches. Millimeters are for general information only.
2. Pin-out: G = gate, S = source, D = drain, and NC = not connected.
3. Index area: A notch or a pin 1 identification mark shall be located adjacent to pin 1. The manufacturer's identification shall not be used as a pin 1 identification mark.
4. This dimension shall be measured with the device seated in seating plane gauge JEDEC Outline No. GS-3.
5. Lead center when α is 0°. BW₁ shall be measured at the centerline of the leads.
6. Outlines on which the seating plane is coincident with the base plane (LH = 0), terminals lead standoffs are not required, and LW₁ may equal LW along any part of the lead above the seating/base plane.
7. Leads within .005 inch (0.13 mm) radius of True Position (TP) at gauge plane with maximum material condition and unit installed. Twelve spaces.
8. α applies to spread leads prior to installation.
9. Dimensioning and tolerancing in accordance with ASME Y14.5.

FIGURE 1. Physical dimensions and configuration (MO-036AB).

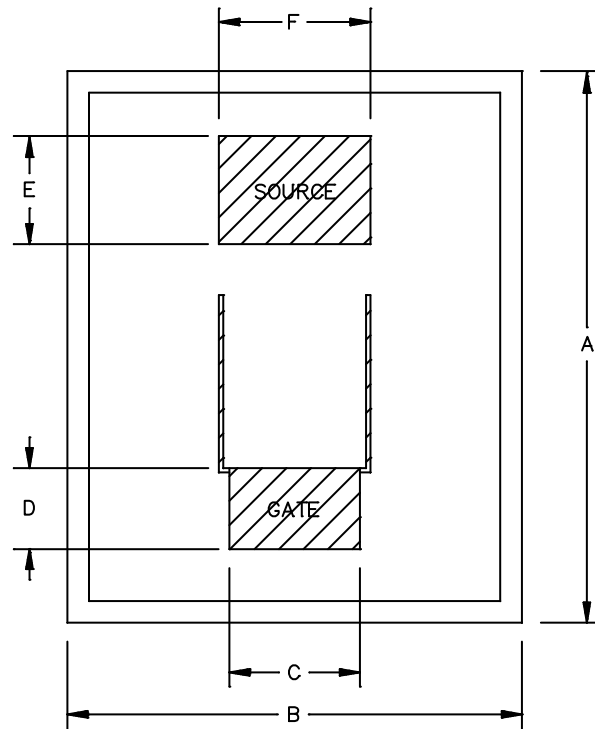


Letter	Dimensions			
	Inches		Millimeters	
	Minimum	Maximum	Minimum	Maximum
A	.082	.092	2.08	2.34
B	.059	.069	1.49	1.75
C	.021	.031	0.53	0.78
D	.013	.023	0.33	0.58
E	.014	.024	0.35	0.61
F	.020	.030	0.51	0.76

NOTES:

1. Dimensions are in inches. Millimeters are given for general information only.
2. Unless otherwise specified, tolerance is $\pm .005$ inch (0.13 mm).
3. The physical characteristics of the die thickness are as follows: The back metals are chromium, nickel, and silver (Cr, Ni, and Ag). The top metal is aluminum (Al).
4. The back contact of the die (not shown) is the drain.
5. Die thickness is .0187 inch (0.475 mm) $\pm .001$ inch (0.025 mm).
6. Dimensioning and tolerancing in accordance with ASME Y14.5.

FIGURE 2. Physical dimensions of die JANHCA and JANKCA (A version).



Letter	Dimensions			
	Inches		Millimeters	
	Minimum	Maximum	Minimum	Maximum
A	.082	.089	2.08	2.26
B	.062	.066	1.58	1.68
C	.019	.021	0.48	0.53
D	.012	.014	0.30	0.36
E	.013	.015	0.33	0.38
F	.022	.024	0.56	0.61

NOTES:

1. Dimensions are in inches. Millimeters are given for general information only.
2. Unless otherwise specified, tolerance is ± 0.005 inch (0.13 mm).
3. The physical characteristics of the die are as follows: The back metals are chromium, nickel, and silver (Cr, Ni, and Ag). The top metal is aluminum (Al).
4. The back contact of the die (not shown) is the drain.
5. Die thickness is .015 inch (0.38 mm) ± 0.001 inch (0.025 mm).
6. Dimensioning and tolerancing in accordance with ASME Y14.5.

FIGURE 3. Physical dimensions of die JANHCB and JANKCB (B-version).

3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in [MIL-PRF-19500](#) and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see [4.2](#) and [6.3](#)).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in [MIL-PRF-19500](#).

I_{AS} Rated avalanche current, nonrepetitive.
nC nano coulomb.

3.4 Interface and physical dimensions. The interface requirements and physical dimensions shall be as specified in [MIL-PRF-19500](#) and on [figure 1](#) (MO-036AB) and [figures 2](#) and [3](#) (unencapsulated die) herein.

3.4.1 Lead finish. Unless otherwise specified, the lead finish shall be solderable as defined in [MIL-STD-750](#), [MIL-PRF-19500](#), and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see [6.2](#)).

3.4.2 Pin out. The pin out of the device types shall be as shown on [figures 1](#), [2](#), and [3](#).

3.5 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in [1.3](#), [1.4](#), and [table I](#) herein.

3.5.1 Electrostatic discharge protection. The devices covered by this specification require electrostatic protection.

3.5.2 Handling. MOS devices must be handled with certain precautions to avoid damage due to the accumulation of electrostatic charge. The following handling practices shall be followed:

- a. Devices shall be handled on benches with conductive handling devices.
- b. Ground test equipment, tools, and personnel handling devices.
- c. Do not handle devices by the leads.
- d. Store devices in conductive foam or carriers.
- e. Avoid use of plastic, rubber, or silk in MOS areas.
- f. Maintain relative humidity above 50 percent if practical.
- g. Care shall be exercised, during test and troubleshooting, to apply not more than maximum rated voltage to any lead.
- h. Gate must be terminated to source, $R \leq 100 \text{ k}\Omega$, whenever bias voltage is to be applied drain to source.

3.6 Electrical test requirements. The electrical test requirements shall be as specified in [table I](#).

3.7 Marking. Marking shall be in accordance with [MIL-PRF-19500](#).

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4 and tables I and II).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500, and as specified herein.

4.2.1 JANHC and JANKC devices. Qualification for JANHC and JANKC devices shall be as specified in MIL-PRF-19500.

4.2.2 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of table II tests, the tests specified in table II herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

4.3 Screening.

4.3.1 Screening of packaged devices (quality levels JANS, JANTX and JANTXV only). Screening of packaged devices shall be in accordance with table E-IV of [MIL-PRF-19500](#), and as specified herein. The following measurements shall be made in accordance with [table I](#) herein. Devices that exceed the limits of [table I](#) herein shall not be acceptable.

Screen (see table E-IV of MIL-PRF-19500)	Measurement (1) (2)	
	JANS level	JANTX and JANTXV levels
(3)	Gate stress test (see 4.3.1.1).	Gate stress test (see 4.3.1.1).
(3) (4)	Method 3470 of MIL-STD-750 , (see 4.3.1.2) optional.	Method 3470 of MIL-STD-750 , (see 4.3.1.2) optional.
3c (3)	Method 3161 of MIL-STD-750 , (see 4.3.1.3).	Method 3161 of MIL-STD-750 , (see 4.3.1.3).
9	I_{GSSF1} , I_{GSSR1} , I_{DSS1} , see table I , subgroup 2 herein.	See table I , subgroup 2 herein.
10	Method 1042 of MIL-STD-750 , test condition B.	Method 1042 of MIL-STD-750 , test condition B.
11	I_{GSSF1} , I_{GSSR1} , I_{DSS1} , $r_{DS(on)1}$, $V_{GS(th)1}$ subgroup 2 of table I herein; $\Delta I_{GSSF1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 25$ μ A dc or ± 100 percent of initial value, whichever is greater.	I_{GSSF1} , I_{GSSR1} , I_{DSS1} , $r_{DS(on)1}$, $V_{GS(th)1}$ subgroup 2 of table I herein.
12	Method 1042 of MIL-STD-750 , test condition A, $t = 240$ hours	Method 1042 of MIL-STD-750 , test condition A.
13	Subgroups 2 and 3 of table I herein; $\Delta I_{GSSF1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 25$ μ A dc or ± 100 percent of initial value, whichever is greater. $\Delta r_{DS(on)1} = \pm 20$ percent of initial value. $\Delta V_{GS(th)1} = \pm 20$ percent of initial value.	Subgroup 2 of table I herein; $\Delta I_{GSSF1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 25$ μ A dc or ± 100 percent of initial value, whichever is greater. $\Delta r_{DS(on)1} = \pm 20$ percent of initial value. $\Delta V_{GS(th)1} = \pm 20$ percent of initial value.

- (1) At the end of the test program, I_{GSSF1} , I_{GSSR1} and I_{DSS1} are measured.
- (2) An out-of-family program to characterize I_{GSSF1} , I_{GSSR1} , I_{DSS1} and $V_{GS(th)1}$ shall be invoked.
- (3) Shall be performed anytime before screen 9.
- (4) This test method in no way implies a repetitive avalanche energy rating. This test need not be performed in group A when performed as a screen.

4.3.1.1 Gate stress test. Apply $V_{GS} = +30$ V minimum for $t = 250$ μ s minimum.

4.3.1.2 Single pulse avalanche energy (E_{AS}). The single pulse avalanche energy capability shall be determined in accordance with method 3470 of [MIL-STD-750](#). The following details shall apply:

- a. Peak current (I_{AS}) I_{D1} .
- b. Peak gate voltage (V_{GS}) 10 V.
- c. Gate to source resistor (R_{GS}) $25 \leq R_{GS} \leq 200\Omega$.
- d. Initial case temperature $+25^\circ\text{C}$ $+10^\circ\text{C}$, -5°C .
- e. Inductance $\left[\frac{2E_{AS}}{(I_{D1})^2} \right] \left[\frac{V_{BR}-V_{DD}}{V_{BR}} \right]$ mH minimum
- f. Number of pulses to be applied 1 pulse minimum.
- g. Supply voltage (V_{DD}) 25 V minimum.

4.3.1.3 Thermal impedance. The thermal impedance measurements shall be performed in accordance with method 3161 of [MIL-STD-750](#) using the guidelines in that method for determining I_M , I_H , t_H , t_{SW} , (and V_H where appropriate). Measurement delay time (t_{MD}) = 70 μ s maximum. (See [figure 5](#) herein for thermal response curves.) See [table II](#), group E, subgroup 4 herein.

4.3.2 Screening of unencapsulated die (JANHNC and JANKC). Screening of JANHC and JANKC unencapsulated die shall be in accordance with appendix G of [MIL-PRF-19500](#). The burn-in duration for JANKC level shall follow the JANS requirements; the JANHC level shall follow the JANTX requirements of table E-IV of [MIL-PRF-19500](#). As a minimum, die shall be 100 percent probed in accordance with group A.

4.4 Conformance inspection. Conformance inspection shall be in accordance with [MIL-PRF-19500](#), and as specified herein. Alternate flow is allowed for quality conformance inspection in accordance with appendix E of [MIL-PRF-19500](#).

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with table E-V of [MIL-PRF-19500](#), and [table I](#) herein. End-point electrical measurements shall be in accordance with [table I](#), subgroup 2 herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VIA (JANS) and table E-VIB (JAN, JANTX, and JANTXV) of [MIL-PRF-19500](#), and herein. Electrical measurements (end-points) shall be in accordance with [table I](#), subgroup 2 herein.

4.4.2.1 Quality level JANS (table E-VIA of [MIL-PRF-19500](#)).

Subgroup	Method	Conditions
B3	1051	Condition G.
B5	1042	Gate stress; condition B, $V_{GS} = 80$ percent of rated, $T_A = +175^\circ\text{C}$, $t = 24$ hours.
B5	1042	Reverse bias, condition A, $V_{DS} = 80$ percent of rated, $T_A = +175^\circ\text{C}$, $t = 120$ hours.

4.4.2.2 Quality levels JAN, JANTX, and JANTXV (table E-VIB of MIL-PRF-19500).

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
B2	1051	Condition G.
B3	1042	Condition D, the heating cycle shall be 1 minute minimum.
B5 and B6		Not applicable.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VII of MIL-PRF-19500 and as follows herein. Electrical measurements (end-points) shall be in accordance with [table I](#), subgroup 2 herein.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
C2	2036	Condition E: The sampling plan applies to the number of leads tested. A minimum of three devices shall be tested.
C5	3161	See 4.3.1.3 .
C6	1042	Condition D, the heating cycle shall be 1 minute minimum.

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-IX of MIL-PRF-19500 and as specified in [table II](#) herein. Electrical measurements (end-points) shall be in accordance with [table I](#), subgroup 2 herein.

4.5 Method of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse response measurements. Conditions for pulse response measurement shall be as specified in section 4 of [MIL-STD-750](#).

4.5.2 Thermal resistance. Thermal resistance measurements shall be performed in accordance with method 3161 of [MIL-STD-750](#). $R_{\theta JA1}$ maximum = 90°C/W, for each die.

- a. I_M measuring current 10 mA.
- b. I_H drain heating current 0.15 A minimum.
- c. t_H heating time Steady-state (see method 3161 of [MIL-STD-750](#) for definition).
- d. V_H drain-source heating voltage 15 V minimum.
- e. t_{MD} measurement time delay 30 to 60 μ s.
- f. t_{SW} sample window time 10 μ s maximum.

TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Max	Min	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Thermal impedance <u>2/</u>	3161	See 4.3.1.3	$Z_{\theta JC}$			
Breakdown voltage, drain-to-source	3407	Bias condition C $V_{GS} = 0$ V dc, $I_D = 1$ mA dc,	$V_{(BR)DSS}$	100		V dc
Gate-to-source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$, $I_D = 0.25$ mA dc	$V_{GS(th)1}$	2.0	4.0	V dc
Gate current (forward)	3411	Bias condition C, $V_{GS} = +20$ V dc, $V_{DS} = 0$	I_{GSSF1}		+100	nA dc
Gate current (reverse)	3411	Bias condition C, $V_{GS} = -20$ V dc, $V_{DS} = 0$	I_{GSSR1}		-100	nA dc
Drain current	3413	Bias condition C, $V_{GS} = 0$ V dc, $V_{DS} = 80$ percent of rated V_{DS}	I_{DSS1}		25	μ A dc
Static drain-to-source on-state resistance	3421	Bias condition A, $V_{GS} = 10$ V dc, $I_D = \text{rated } I_{D2}$ (see 1.3), pulsed (see 4.5.1)	$r_{DS(on)1}$		0.70	Ω
		$I_D = I_{D1}$ (see 1.3)	$r_{DS(on)2}$		0.80	Ω
Forward voltage	4011	$V_{GS} = 0$ V, $I_D = I_{D1}$, pulsed (see 4.5.1)	V_{SD}		1.5	V
<u>Subgroup 3</u>						
High temperature operation:		$T_C = T_J = +125^\circ\text{C}$				
Gate current	3411	Bias condition C, $V_{GS} = +20$ V dc and -20 V dc, $V_{DS} = 0$ V dc	I_{GSS2}		± 200	nA dc
Drain current	3413	Bias condition C, $V_{GS} = 0$ V dc, $V_{DS} = 80$ percent of rated V_{DS}	I_{DSS2}		0.25	mA dc
Static drain-to-source on-state resistance	3421	Bias condition A, $V_{GS} = 10$ V dc, $I_D = \text{rated } I_{D2}$, pulsed (see 4.5.1),	$r_{DS(on)3}$		1.4	Ω

See footnotes at end table.

TABLE I. Group A inspection – Continued.

Inspection 1/	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Max	Min	
Subgroup 3 – Continued						
Gate-to-source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$, $I_D = 0.25$ mA dc	$V_{GS(th)2}$	1.0		V dc
Low temperature operation:						
Gate-to-source voltage (threshold)	3403	$T_C = T_J = -55^{\circ}\text{C}$ $V_{DS} \geq V_{GS}$, $I_D = 0.25$ mA dc	$V_{GS(th)3}$		5.0	V dc
Subgroup 4						
Switching time test	3472	$I_D = \text{rated } I_{D1}$, $V_{GS} = 10$ V dc, $R_g = 7.5\Omega$, $V_{DD} = 50$ percent of $V_{BR(DSS)}$				
Turn-on delay time			$t_{d(on)}$		20	ns
Rise time			t_r		25	ns
Turn-off delay time			$t_{d(off)}$		40	ns
Fall time			t_f		40	ns
Subgroup 5						
Single pulse unclamped inductive switching 3/	3470	See 4.3.1.2 , $n = 116$, $c = 0$	E_{AS}			
Electrical measurements		See subgroup 2 of this table				
Safe operating area test for power MOSFETs	3474	$V_{DS} = 80$ percent of rated $V_{BR(DSS)}$, $I_D = .25$ A, $t_p = 10$ ms, (see figure 6)				
Electrical measurements		See subgroup 2 of this table				
Subgroup 6						
Not applicable						

See footnotes at end table.

TABLE I. Group A inspection – Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Max	Min	
<u>Subgroup 7</u>						
Gate charge	3471	Condition B				
On-state gate charge			$Q_{g(on)}$		15	nC
Gate to source charge			Q_{gs}		7.5	nC
Gate to drain charge	3473	Condition A, $d_i/d_t = 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq 30 \text{ V dc}$; $I_D = I_{D1}$, (see 1.3)	Q_{gd}		7.5	nC
Reverse recovery time			t_{rr}		200	ns

1/ For sampling plan, see [MIL-PRF-19500](#).

2/ This test is required for the following end-point measurement only (not intended for screen 9 or 11): JANS, table E-VIA of [MIL-PRF-19500](#), group B, subgroup 3; JAN, JANTX, and JANTXV, table E-VIB of [MIL-PRF-19500](#), group B, subgroup 2; and table E-VII of [MIL-PRF-19500](#), group C, subgroup 2, and table E-IX of [MIL-PRF-19500](#), group E, subgroup 1.

3/ This test need not be performed in group A if performed in screening.

TABLE II. Group E inspection (all quality levels) for qualification or re-qualification only. 1/

Inspection	MIL-STD-750		Sample plan
	Method	Conditions	
<u>Subgroup 1</u>			45 devices c = 0
Temperature cycling (air to air)	1051		
Hermetic seal Fine leak Gross leak	1071		
Electrical measurements		See table I , subgroup 2.	
<u>Subgroup 2 2/</u>			45 devices c = 0
Steady-state reverse bias	1042	Condition A, 1,000 hours.	
Electrical measurements		See table I , subgroup 2.	
Steady-state gate bias	1042	Condition B, 1,000 hours	
Electrical measurements		See table I , subgroup 2.	
<u>Subgroup 4</u>			Sample size N/A
Thermal impedance curves		See MIL-PRF-19500 .	
<u>Subgroup 5</u>			
Not applicable			
<u>Subgroup 6</u>			11 devices
Electrostatic discharge sensitivity	1020		
<u>Subgroup 11</u>			22 devices c = 0
Test procedure for measuring dv/dt during reverse recovery of power MOSFET transistors	3476	Test conditions shall be derived by the manufacturer.	

1/ JANHC and JANKC devices are qualified in accordance with appendix G of [MIL-PRF-19500](#).

2/ A separate sample for each test may be selected.

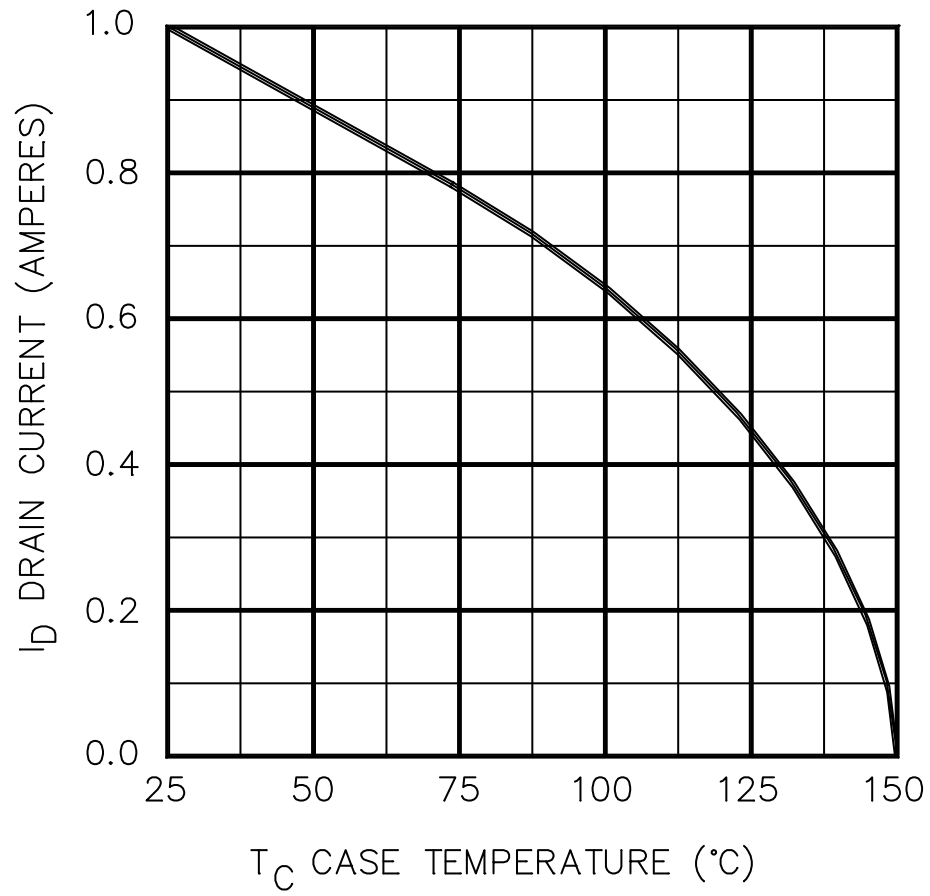
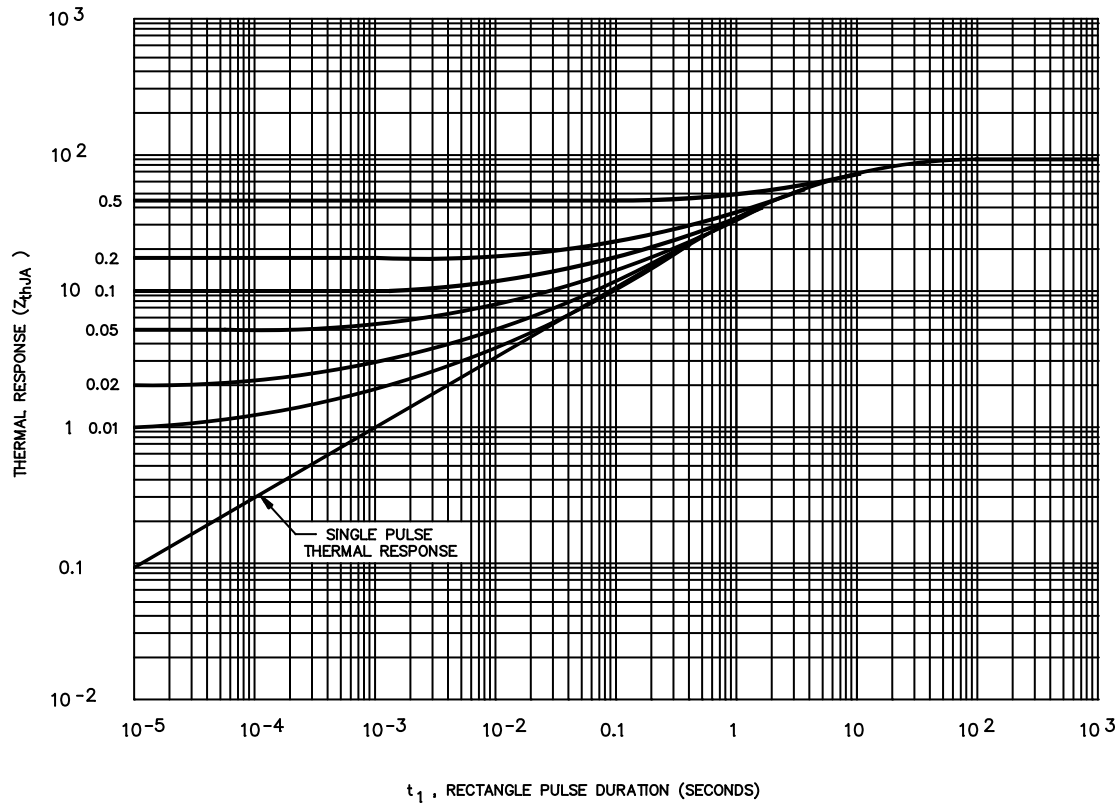


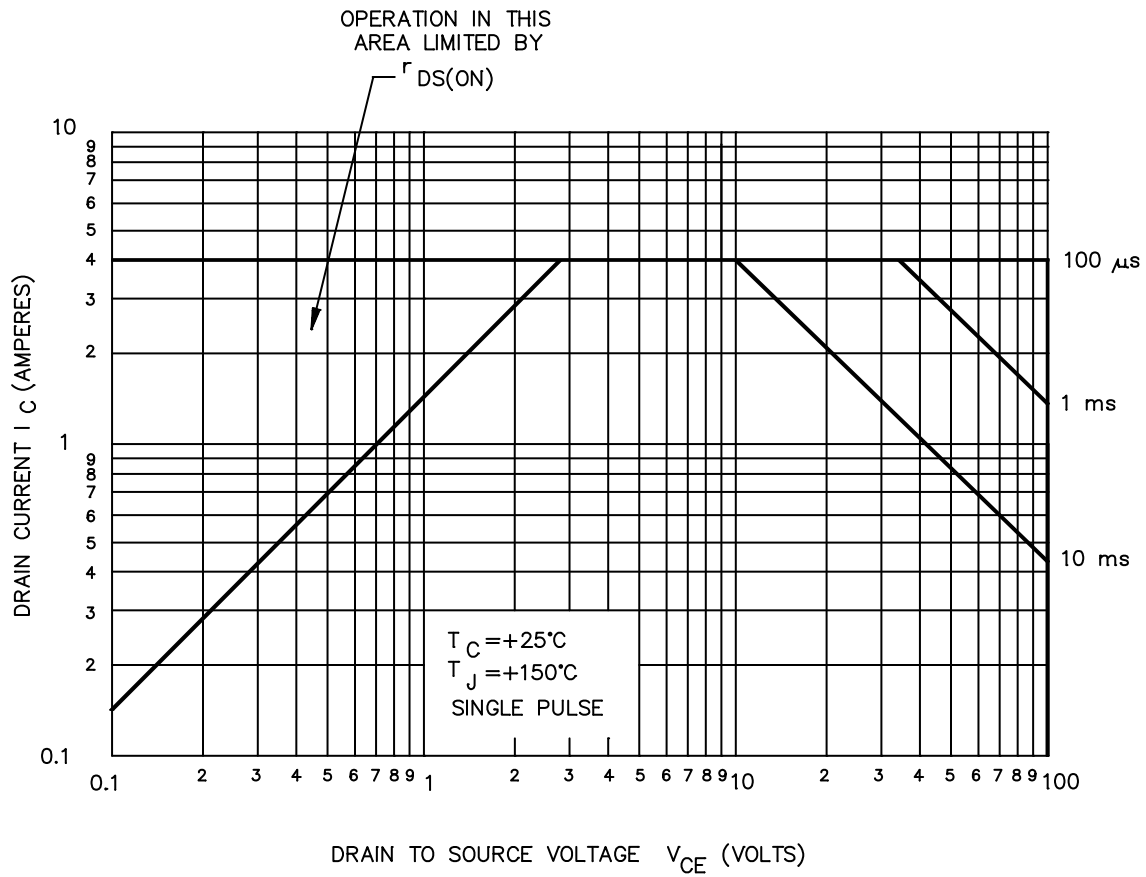
FIGURE 4. Maximum drain current versus case temperature.



NOTES:

1. The curves are from bottom to top are: Single pulse, $D = 0.01$, $D = 0.02$, $D = 0.05$, $D = 0.1$, and $D = 0.5$.
2. Pulse duration magnitude = P_{DM} .
3. Duty factor $D = t_1 / t_2$.
4. Peak $T_J = P_{DM} \times Z_{thJA} + T_C$.

FIGURE 5. Thermal response curves.

FIGURE 6. Safe operating area.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in [MIL-PRF-19500](#) are applicable to this specification.)

6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see [3.4.1](#)).
- d. The complete Part or Identifying Number (PIN), see title and section [1](#).
- e. For die acquisition, the JANHC or JANKC letter version shall be specified (see [figures 2 and 3](#)).

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List ([QML-19500](#)) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DLA Land and Maritime, ATTN: VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail vqe.chief@dla.mil. An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://assist.dla.mil>.

6.4 Suppliers of JANHC and JANKC. The qualified JANHC and JANKC die suppliers with the applicable letter version (example JANHCA2N7334) will be identified on the QML.

JANC ordering information		
PIN	Manufacturers	
	59993	43611
2N7334	JANHCA2N7334 (1) JANKCA2N7334 (1)	JANHCB2N7334 (1) JANKCB2N7334 (1)

- (1) The JANHC2N7334 and the JANKC2N7334 die were never qualified for listing on [QML-19500](#).

6.5 Substitution information. Devices covered by this specification are substitutable for the manufacturers' and users' PIN. This information in no way implies that manufacturers' part or identifying numbers are suitable as a substitute for the military PIN's.

Military PIN	Manufacturer's CAGE code	Manufacturer's and user's PIN
2N7334	59993	IRFG110

6.6 Changes from previous issue. The margins of this specification are marked with vertical lines to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the previous issue.

Custodians:
 Army – CR
 Navy – EC
 Air Force – 85
 NASA – NA
 DLA – CC

Preparing activity:
 DLA – CC
 (Project 5961-2014-091)

Review activities:
 Army – MI, SM
 Navy – MC
 Air Force – 19, 99

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.dla.mil>.